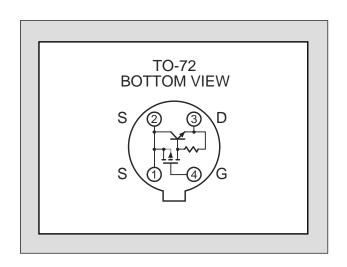


# Linear Integrated Systems

| FEATURES                               |                          |  |  |  |  |  |
|--|--------------------------|--|--|--|--|--|
| HIGH INPUT IMPEDANCE                   | $r_{Gs}$ = 100G $\Omega$ |  |  |  |  |  |
| HIGH TRANSCONDUCTANCE                  | $Y_{FS} = 30,000 \mu S$  |  |  |  |  |  |
| ABSOLUTE MAXIMUM RATINGS <sup>1</sup>  |                          |  |  |  |  |  |
| @ 25 °C (unless otherwise stated)      |                          |  |  |  |  |  |
| Maximum Temperatures                   |                          |  |  |  |  |  |
| Storage Temperature                    | -65 to +150 °C           |  |  |  |  |  |
| Operating Junction Temperature         | -55 to +125 °C           |  |  |  |  |  |
| Maximum Power Dissipation              |                          |  |  |  |  |  |
| Continuous Power Dissipation @ +125 °C | 200mW                    |  |  |  |  |  |
| Maximum Currents                       |                          |  |  |  |  |  |
| Drain Current                          | $I_D = 25mA$             |  |  |  |  |  |
| Maximum Voltages                       |                          |  |  |  |  |  |
| Drain to Source <sup>1</sup>           | V <sub>DSO</sub> = 20V   |  |  |  |  |  |
| Gate to Source                         | V <sub>GSS</sub> = 20V   |  |  |  |  |  |

# **LS320**

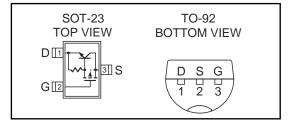
## HIGH INPUT IMPEDANCE **BIFET AMPLIFIER**



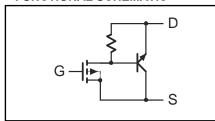
## ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

| SYMBOL           | CHARACTERISTIC                         | MIN    | TYP | MAX | UNITS | CONDITIONS   |
|------------------|--|--------|-----|-----|-------|--|
| $V_{DS}$         | Drain to Source Voltage                | -20    |     |     | V     | $I_{DS} = 100 \mu A, V_{GS} = 0 V$                               |
| $V_{GS}$         | Gate to Source Voltage                 | -12    | -10 | -7  | V     | $I_{DS} = 10 \text{mA}, V_{gs} = -10 V^{2,3}$                    |
| g <sub>fs</sub>  | Common Source Forward Transconductance | 30,000 |     |     | μS    | $I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}, f = 1 \text{kHz}$ |
| goss             | Common Source Output Conductance       |        | 300 |     | μS    | $I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}, f = 1 \text{kHz}$ |
| $r_{Gs}$         | Gate to Source Input Resistance        | 100    |     |     | GΩ    | $V_{GS}$ = 0 to 20V, $T_J$ to 125 °C                             |
| C <sub>ISS</sub> | Input Capacitance                      |        | 8   |     | pF    | $I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}$                   |
| C <sub>RSS</sub> | Reverse Transfer Capacitance           |        | 1.5 |     | pF    | $I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}$                   |
| e <sub>n</sub>   | Noise Voltage                          |        | 25  |     | μV    | $I_{DS}$ = 10mA, $V_{DS}$ = 10V<br>BW = 50 to 15kHz              |

### **PACKAGE OPTIONS**



### **FUNCTIONAL SCHEMATIC**



- Absolute maximum ratings are limiting values above which serviceability may be impaired.
- The gate to source voltage must never exceed 100V, t < 10ms.
- 3. Additional screening available

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